IN THE CLAIMS

1. **(Original)** A method of forming a semiconductor thin-film, comprising:

irradiating a first laser beam to a semiconductor thin-film to form a first irradiated region; and

irradiating a second laser beam to the thin-film in such a way as not to overlap with the first irradiated region, thereby forming a second irradiated region and a non-irradiated region;

wherein the second laser beam is irradiated to the thin-film to be coaxial with the first laser beam;

and wherein an alignment mark is formed by using an optical constant difference between the second irradiated region and the non-irradiated region.

2. **(Original)** The method according to claim 1, wherein the second laser beam is controlled in such a way that the second irradiated region is solid.

3. **(Original)** The met according to claim 1, wherein the second laser beam is controlled in such a way that the second irradiated region is hollow due to ablation.

4. **(Original)** The method according to claim 1, wherein the first irradiated region serves as an annealed semiconductor region, in which an active region of a TFT is formed.

5. **(Original)** The method according to claim 1, wherein the semiconductor thin-film is made of a-Si (amorphous silicon).

6. **(Original)** The method according to claim 1, wherein the semiconductor thin-film is made of poly-Si (polysilicon).

7. **(Original)** The method according to claim 1, wherein an excimer laser is used to generate the first laser beam.

8. **(Original)** A method of forming a semiconductor thin-film, comprising:

irradiating a first laser beam to a semiconductor thin-film to form a first irradiated region; and

irradiating a second laser beam to the thin-film in such a way as to overlap with the first irradiated region, thereby forming a second irradiated region;

wherein the second laser beam is irradiated to the thin-film to be coaxial with the first laser beam;

and wherein an alignment mark is formed by using an optical constant difference between the first irradiated region and the second irradiated region or between the second irradiated region and a remaining non-irradiated region of the thin-film.

9. **(Original)** The method according to claim 8, wherein the second laser beam is controlled in such a way that the second irradiated region is solid.

10. **(Original)** The method according to claim 8, wherein the second laser beam is controlled in such a way that the second irradiated region is hollow due to ablation.

11. (Original) The method according to claim 8, wherein the first irradiated region serves as a annealed semiconductor region, in which an active region of a TFT is formed.

12. (Original) The method according to claim 8, wherein the semiconductor thin-film is made of a-Si (amorphous silicon).

13. (Original) The method according to claim 8, wherein the semiconductor thin-film is made of poly-Si film (polysilicon).

14. (Original) The method according to claim 8, wherein an excimer laser is used to generate the first laser beam.

15. (Original) The method of forming a semiconductor thin-film, comprising:

irradiating a first laser beam to a whole semiconductor thin-film to form a first irradiated region; and

irradiating a second laser beam to the thin-film in such a way as to overlap with the first irradiated region, thereby forming a second irradiated region;

wherein the second laser beam is irradiated to the thin-film to be coaxial with the first laser beam;

and wherein an alignment mark is formed by using an optical constant difference between the first irradiated region and the second irradiated region.

16. **(Original)** The method according to claim 15, wherein the second laser beam is controlled in such a way that the second irradiated region is solid.

17. **(Original)** The method according to claim 15, wherein the second laser beam is controlled in such a way that the second irradiated region is hollow due to ablation.

18. **(Original)** The method according to claim 15, wherein the first irradiated region serves as an annealed semiconductor region, in which an active region of a TFT is formed.

19. **(Original)** The method according to claim 15, wherein the semiconductor thin-film is made of a-Si (amorphous silicon).

20. **(Original)** The method according to claim 15, wherein the semiconductor thin-film is made of poly-Si (polysilicon).

21. **(Original)** The method according to claim 15, wherein an excimer laser is used to generate the first laser beam.

22. **(Currently Amended)** A laser apparatus comprising:

a movable stage on which a target is place;

a first laser beam generate for generating a first laser beam;

the first laser beam being configured by a first optical system to be irradiated to a semiconductor thin-film as the target on the stage;

a second laser beam generator for generating a second laser beam; and

the second laser beam being configured by a second optical system to be irradiated to the thin-film in such a way as to be coaxial with the first laser ~~beam.~~ beam when a movable optical element included in the second optical system is positioned in a first position in an optical path of the first laser beam.

23. (Currently Amended) The apparatus according to ~~the~~ claim 22, wherein the first laser beam generator and the second laser beam generator are different in size from each other.

24. (Currently Amended) The apparatus according to ~~the~~ claim 22, wherein an excimer laser is used as the first laser beam generator.

25. (Currently Amended) The apparatus according to ~~the~~ claim 22, wherein the ~~second optical system for the second laser beam includes an~~ optical element included in the second optical system is movable between ~~a~~ the first position in ~~an~~ the optical path of the first laser beam and a second position outside the same optical path.

26. (Currently Amended) The apparatus according to ~~the~~ claim 22, wherein when the first laser beam is irradiated to the target, the element is in the second position;

and wherein when the second laser beam is irradiated to the target, the element is in the first position.